



Solid State Devices, Inc.

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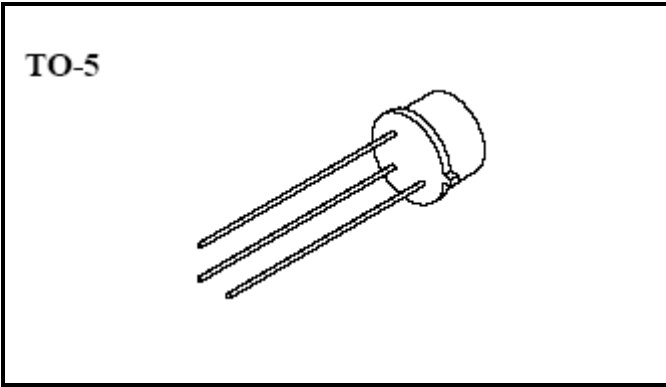
SFS2326 thru SFS2329

**1.6 AMPS
200 – 400 VOLTS
SILICON CONTROLLED
RECTIFIER**

Designer's Data Sheet

FEATURES:

- Low-Level Gate Characteristics
- $I_{GT} = 200 \mu A$ (Max) @ 25°C
- Low Holding Current $I^H = 1 mA$ (Max) @ 25°C
- Anode Common to Case
- Hermetically Sealed



MAXIMUM RATINGS		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SFS2326	V_{DRM}	200	Volts
	SFS2327		250	
	SFS2328	V_{RRM}	300	
	SFS2329		400	
Non-Repetitive Peak Reverse Blocking Voltage (t < 5.0 ms)	SFS2326	V_{RSM}	300	Volts
	SFS2327		350	
	SFS2328		400	
	SFS2329		500	
RMS On-State Current (All Conduction Angles)		$I_T (RMS)$	1.6	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz, T _C = 80°C)		I_{TSM}	15	Amps
Peak Gate Power		P_{GM}	0.1	Watts
Average Gate Power		$P_{G(AV)}$	0.01	Watts
Peak Gate Current		I_{GM}	0.1	Amps
Peak Gate Voltage		V_{GM}	6.0	Volts
Operating Junction Temperature Range		T_J	-65 to +125	°C
Storage Temperature Range		T_{stg}	-65 to +150	°C
Thermal Resistance, Junction to Case		$R_{\theta JC}$	30	°C/W

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SCR004A

DOC



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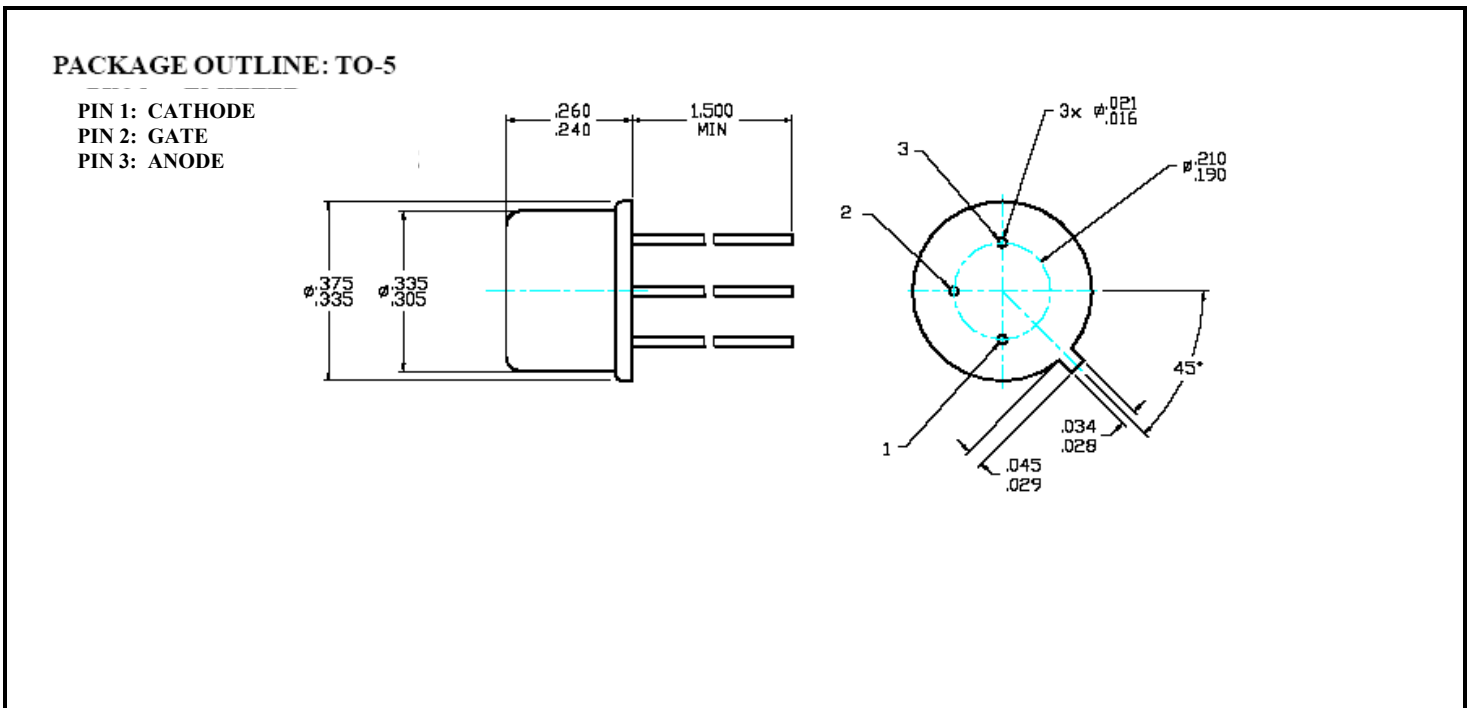
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SFS2326 thru SFS2329

ELECTRICAL CHARACTERISTICS	Symbol	Min	Max	Unit
Peak Reverse Blocking Current (Rated V_{RRM} , $T_C = 25^\circ\text{C}$)	I_{RRM}	—	0.75	μA
Peak Forward Blocking Current (Rated V_{RRM} , $T_C = 25^\circ\text{C}$) (Rated V_{RRM} , $T_C = 125^\circ\text{C}$)	I_{DRM}	—	1 100	μA
Peak On-State Voltage ($I_F = 1.6 \text{ A Peak}$)	V_{TM}	—	1.3	Volts
Gate Trigger Current ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = 125^\circ\text{C}$) ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = -65^\circ\text{C}$)	I_{GT}	— —	200 350	μA
Gate Trigger Voltage ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = 25^\circ\text{C}$) ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = -65^\circ\text{C}$) ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = 125^\circ\text{C}$)	V_{GT}	— — 0.1	0.7 0.9 0.9	Volts
Holding Current ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = 25^\circ\text{C}$) ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = -65^\circ\text{C}$) ($V_D = 6 \text{ V}_{DC}$, $R_L = 100 \Omega$, $T_C = 125^\circ\text{C}$)	I_H	0.8 1.5 0.15	2.0 3.0 —	mA

NOTES:

* RGK current is not included in measurement



*For information on curves, contact the Factory Representative for Engineering Assistance.